# **VN2406L**

**Preferred Device** 

# Small Signal MOSFET 200 mAmps, 240 Volts

N-Channel TO-92

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	240	Vdc
Drain-Gate Voltage	V <sub>DGR</sub>	240	Vdc
Gate–Source Voltage  – Continuous  – Non–repetitive (t <sub>p</sub> ≤ 50 μs)	V <sub>GS</sub> V <sub>GSM</sub>	± 20 ± 40	Vdc Vpk
Continuous Drain Current	ID	200	mAdc
Pulsed Drain Current	IDM	500	mAdc
Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	350 2.8	mW mW/°C
Operating and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	ı	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	312.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	TL	300	°C

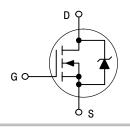


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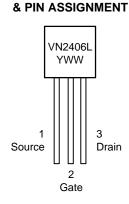
http://onsemi.com

200 mAMPS 240 VOLTS RDS(on) = 6  $\Omega$ 

#### N-Channel







Y = Year WW = Work Week

#### **ORDERING INFORMATION**

Device	Package	Shipping		
VN2406L	TO-92	1000 Units/Box		
VN2406LZL1	TO-92	2000 Ammo Pack		

**Preferred** devices are recommended choices for future use and best overall value.

### VN2406L

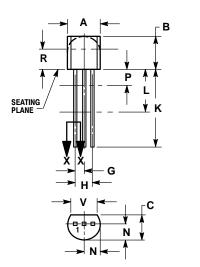
## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

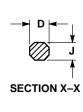
	Symbol	Min	Max	Unit	
STATIC CHARACTERISTICS		1		•	
Drain-Source Breakdown Voltage (V <sub>GS</sub> = 0, I <sub>D</sub> = 100 μA)		V <sub>(BR)</sub> DSS	240		Vdc
Zero Gate Voltage Drain Current (VDS = 120 Vdc, VGS = 0) (VDS = 120 Vdc, VGS = 0, TA	I <sub>DSS</sub>	- -	10 500	μAdc	
Gate- Body Leakage (V <sub>DS</sub> = 0, V <sub>GS</sub> = ±15 V)	lgss	-	±100	nAdc	
Gate Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1.0 mA)	VGS(th)	0.8	2.0	Vdc	
On–State Drain Current (Note 1) (VGS = 10 V, VDS $\geq$ 2.0 VDS(0	I <sub>D(on)</sub>	1.0	-	Adc	
Drain–Source On Resistance (Note 1) $(V_{GS} = 2.5 \text{ V}, I_D = 0.1 \text{ A})$ $(V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A})$		r <sub>DS(on)</sub>	- -	10 6.0	Ω
Forward Transconductance (Note 1) (V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 A)		9fs	300	_,	mS
DYNAMIC CHARACTERISTIC	cs			*	!
Input Capacitance		C <sub>iss</sub>	_	125	pF
Output Capacitance	(V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>oss</sub>	_	50	pF
Reverse Transfer Capacitance	,	C <sub>rss</sub>	_	20	pF
SWITCHING CHARACTERIS	TICS				
Turn-On Time		t(on)	_	8.0	ns
	$(V_{DD} = 60 \text{ Vdc}, I_D = 0.4 \text{ A}, R_I = 150 \Omega, R_G = 25 \Omega)$	t <sub>(r)</sub>	_	8.0	ns
Turn-Off Time		t(off)	_	23	ns
		t <sub>(f)</sub>	_	34	ns

<sup>1.</sup> Pulse Test; Pulse Width < 300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

#### **PACKAGE DIMENSIONS**

TO-92 CASE 29-11 **ISSUE AL** 





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
v	0.135		3 43	

STYLE 22:
PIN 1. SOURCE
2. GATE
3. DRAIN

#### VN2406L

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